

TO-92 Plastic-Encapsulate Transistors

KTA1270 TRANSISTOR (PNP)

FEATURES

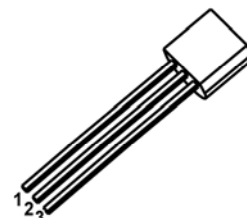
- General Purpose Application Switching Application

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-35	V
V _{CEO}	Collector-Emitter Voltage	-30	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current –Continuous	-0.5	A
P _C	Collector Power Dissipation	500	mW
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

TO-92

1. EMITTER
2. COLLECTOR
3. BASE



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -100μA, I _E =0	-35			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -1mA, I _B =0	-30			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -100μA, I _C =0	-5			V
Collector cut-off current	I _{CB0}	V _{CB} = -35 V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -5 V, I _C =0			-0.1	μA
DC current gain	h _{FE1}	V _{CE} =-1 V, I _C = -100mA	70		240	
	h _{FE2}	V _{CE} =-6 V, I _C = -400mA	25			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -100mA, I _B = -10mA			-0.25	V
Base-emitter voltage	V _{BE(on)}	V _{CE} = -1V, I _C = -100mA			-1	V
Transition frequency	f _T	V _{CE} =-6 V, I _C = -20mA f =100MHz		200		MHz
Collector output capacitance	C _{ob}	V _{CB} =-6V, I _E =0, f=1MHz		13		pF

CLASSIFICATION OF h_{FE}

Rank		O	Y
Range	h _{FE(1)}	70-140	120-240
	h _{FE(2)}	25(min)	40(min)